TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

## TC74VHCT367AF,TC74VHCT367AFN,TC74VHCT367AFT

#### Hex Bus Buffer

TC74VHCT367AF/AFN/AFT

Non-Inverted, 3-State Outputs

The TC74VHCT367A is advanced high speed CMOS HEX BUS BUFFERs fabricated with silicon gate C<sup>2</sup>MOS technology.

They achieve the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

They contain six buffers ;four buffers are controlled by an enable input ( $\overline{G1}$ ), and the other two buffers are controlled by another enable input ( $\overline{G2}$ ). The outputs of each buffer group are enabled when  $\overline{G1}$  and/or  $\overline{G2}$  inputs are held low; if held high, these outputs are in a high impedance state.

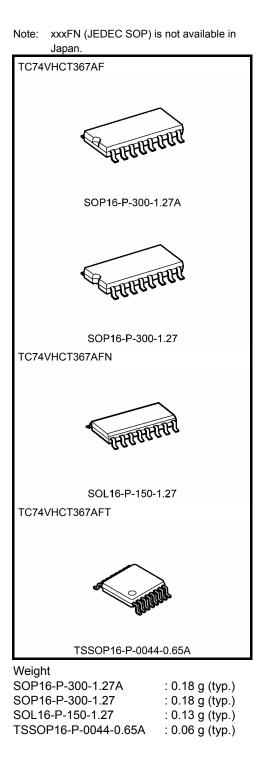
The TC74VHCT367A is a non-inverting output type.

Input protection and output circuit ensure that 0 to 5.5 V can be applied to the input and output <sup>(Note)</sup> pins without regard to the supply voltage. These structure prevents device destruction due to mismatched supply and input/output voltages such as battery back up, hot board insertion, etc.

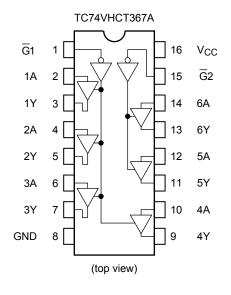
Note: Output in off-state

#### Features

- High speed:  $t_{pd} = 4.7$  ns (typ.) at  $V_{CC} = 5$  V
- Low power dissipation:  $I_{CC} = 4 \mu A \pmod{at Ta} = 25^{\circ}C$
- Compatible with TTL outputs: VIL = 0.8 V (max)  $V_{IH} = 2.0 \ V (min) \label{eq:VIL}$
- Power down protection is provided on all inputs and outputs.
- Balanced propagation delays:  $t_{pLH} \simeq t_{pHL}$
- Low noise:  $V_{OLP} = 0.8 V (max)$
- Pin and function compatible with the 74ALS367.



## **Pin Assignment**



### Truth Table

Inp	uts	Output
IG	А	Y
L	L	L
L	Н	Н
Н	Х	Z

X: Don't care

Z: High impedance

## Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5 to 7.0	V
DC input voltage	V <sub>IN</sub>	-0.5 to 7.0	V
DC output voltage	)/a=	-0.5 to 7.0 (Note 2)	V
DC output voltage	Vout	-0.5 to V <sub>CC</sub> + 0.5 (Note 3)	v
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	IOK	±20 (Note 4)	mA
DC output current	IOUT	±25	mA
DC V <sub>CC</sub> /ground current	ICC	±50	mA
Power dissipation	PD	180	mW
Storage temperature	T <sub>stg</sub>	-65 to 150	°C

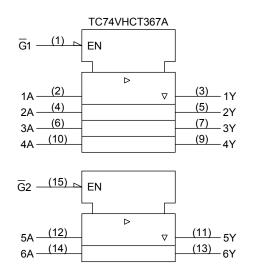
Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Note 2: Output in Off-State

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4:  $V_{OUT} < GND$ ,  $V_{OUT} > V_{CC}$ 

## IEC Logic Symbol



## **Recommended Operating Conditions (Note 1)**

Characteristics	s Symbol Rating		Unit
Supply voltage	V <sub>CC</sub>	4.5 to 5.5	V
Input voltage	V <sub>IN</sub>	0 to 5.5	V
Output voltage	)/a=	0 to 5.5 (Note 2)	V
Output voltage	Vout	0 to V <sub>CC</sub> (Note 3)	v
Operating temperature	T <sub>opr</sub>	-40 to 85	°C
Input rise and fall time	dt/dV	0 to 20	ns/V

Note 1: The recommended operating conditions are required to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Note 2: Output in Off-State

Note 3: High or low state.

## **Electrical Characteristics**

#### **DC Characteristics**

Characteristics Symbol		Test Condition		Ta = 25°C			Ta = −40 to 85°C		Unit	
	-			V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	
High-level input voltage	V <sub>IH</sub>	-		4.5 to 5.5	2.0	—		2.0	—	V
Low-level input voltage	V <sub>IL</sub>	_		4.5 to 5.5	-	_	0.8	-	0.8	V
High-level output	Varia	VIN	I <sub>OH</sub> = -50 μA	4.5	4.40	4.50		4.40		v
voltage		= V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = −8 mA	4.5	3.94	—		3.80	—	
Low-level output	N	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 50 μA	4.5	_	0.0	0.10		0.10	v
voltage	V <sub>OL</sub>		I <sub>OL</sub> = 8 mA	4.5	_	_	0.36	_	0.44	
3-state output off-state current	I <sub>OZ</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or } GND$		5.5	_	_	±0.25	_	±2.50	μA
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V or GND		0 to 5.5	_	_	±0.1	_	±1.0	μA
	ICC	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	_	_	4.0		40.0	μA
Quiescent supply current	Ісст	Per input: V <sub>IN</sub> = 3.4 V Other input: V <sub>CC</sub> or GND		5.5	_	_	1.35	_	1.50	mA
Output leakage current	I <sub>OPD</sub>	V <sub>OUT</sub> = 5.5 V		0		_	+0.5	_	+5.0	μA

#### AC Characteristics (input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = −40 to 85°C		Unit
	<b>- j-</b> - :		$V_{CC}(V)$	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	
Propagation delay	t <sub>pLH</sub>	_	5.0 ± 0.5	15	_	4.7	7.4	1.0	8.5	ns
time	t <sub>pHL</sub>			50	_	5.2	8.4	1.0	9.5	
3-state output enable	t <sub>pZL</sub>	R <sub>L</sub> = 1kΩ	5.0 ± 0.5	15	_	4.9	10.4	1.0	12.0	ns
time	t <sub>pZH</sub>			50	_	5.4	11.4	1.0	13.0	115
3-state output disable time	t <sub>pLZ</sub>	R <sub>L</sub> = 1kΩ	5.0 ± 0.5	50	_	6.3	11.4	1.0	13.0	ns
	t <sub>pHZ</sub>									113
Output to output skew	t <sub>osLH</sub>	(Note 1)	5.0 ± 0.5	50	_	_	1.0	_	1.0	ns
	t <sub>osHL</sub>		5.0 ± 0.5	50			1.0		1.0	113
Input capacitance	CIN		_		-	4	10	-	10	pF
Output capacitance	C <sub>OUT</sub>		_		_	6	_	_	_	pF
Power dissipation capacitance	C <sub>PD</sub>			(Note 2)		16			_	pF

Note 1: Parameter guaranteed by design.

 $t_{OSLH} = |t_{pLHm} - t_{pLHn}|, t_{OSHL} = |t_{pHLm} - t_{pHLn}|$ 

Note 2: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 (per bit)$ 

#### Noise Characteristics (input: t<sub>r</sub> = t<sub>f</sub> = 3 ns)

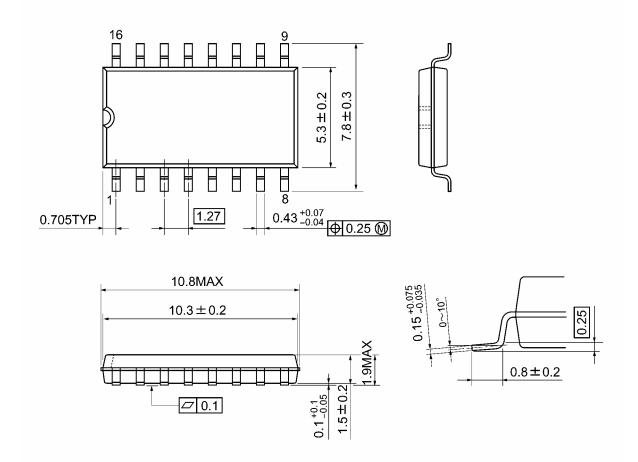
Characteristics	Symbol	Test Condition	Ta =	Unit		
Characteristics	Symbol		V <sub>CC</sub> (V)	Тур.	Max	Unit
Quiet output maximum dynamic $V_{OL}$	V <sub>OLP</sub>	C <sub>L</sub> = 50 pF	5.0	0.6	0.8	V
Quiet output minimum dynamic $V_{OL}$	V <sub>OLV</sub>	C <sub>L</sub> = 50 pF	5.0	-0.6	-0.8	V
Minimum high level dynamic input voltage	VIHD	C <sub>L</sub> = 50 pF	5.0	_	2.0	V
Maximum low level dynamic input voltage	V <sub>ILD</sub>	C <sub>L</sub> = 50 pF	5.0	_	0.8	V



## **Package Dimensions**

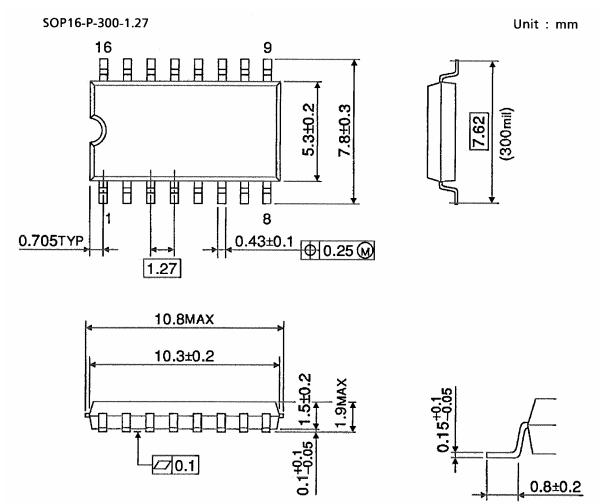
SOP16-P-300-1.27A

Unit: mm



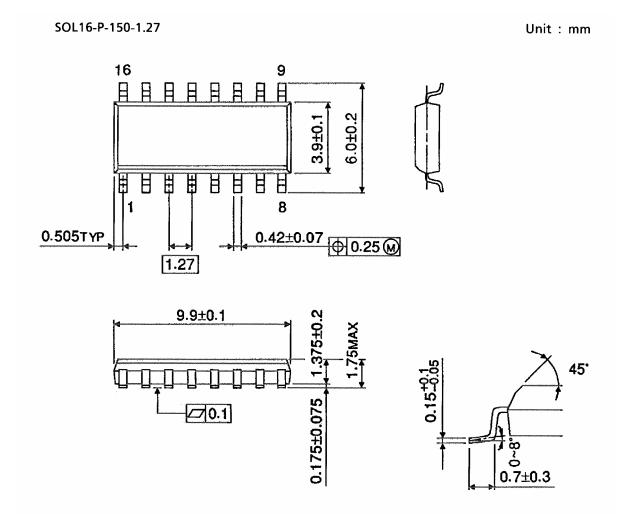
Weight: 0.18 g (typ.)

## **Package Dimensions**



Weight: 0.18 g (typ.)

## Package Dimensions (Note)



Note: This package is not available in Japan.

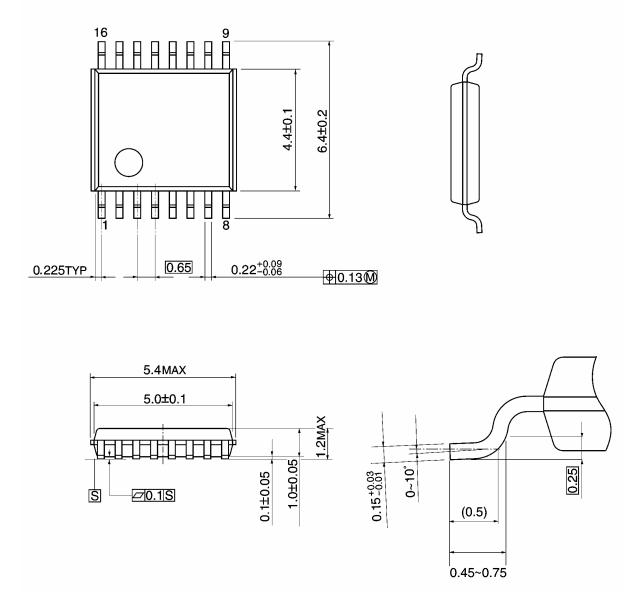
Weight: 0.13 g (typ.)

# **TOSHIBA**

## Package Dimensions

TSSOP16-P-0044-0.65A

Unit: mm



Weight: 0.06 g (typ.)

Note: Lead (Pb)-Free Packages SOP16-P-300-1.27A SOL16-P-150-1.27 TSSOP16-P-0044-0.65A

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